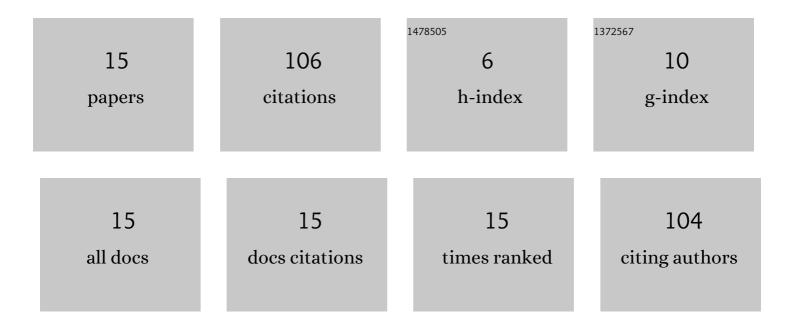
Abdelhakim Latreche

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Modified expressions of field and thermionic-field emission for Schottky barrier diodes in the reverse regime. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2021, 24, 16-21. | 1.0 | 2 |
| 2 | Determination of temperature dependence of electron effective mass in 4H-SiC from reverse current-voltage characteristics of 4H-SiC Schottky barrier diodes. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2020, 23, 271-275. | 1.0 | 1 |
| 3 | Combined thermionic emission and tunneling mechanisms for the analysis of the leakage current for Ga2O3 Schottky barrier diodes. SN Applied Sciences, 2019, 1, 1. | 2.9 | 13 |
| 4 | Validity of the Padovani–Stratton formulas for analysis of reverse current–voltage characteristics of 4H–SiC Schottky barrier diodes. Semiconductor Science and Technology, 2019, 34, 055021. | 2.0 | 5 |
| 5 | Conduction mechanisms of the reverse leakage current of 4H-SiC Schottky barrier diodes. Semiconductor Science and Technology, 2019, 34, 025016. | 2.0 | 10 |
| 6 | Combination of thermionic emission and tunneling mechanisms to analyze the leakage current in 4H-SiC Schottky barrier diodes. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 19-25. | 1.0 | 7 |
| 7 | Conduction mechanisms of the reverse leakage current of β-Ga2O3 Schottky barrier diodes. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 397-403. | 1.0 | 5 |
| 8 | Comment on "Pressure Induced Phase Transition, Elastic and Thermal Properties of Rare Earth Tellurides― Transactions of the Indian Institute of Metals, 2017, 70, 1159-1160. | 1.5 | 1 |
| 9 | Comment on "Density functional investigation on electronic structure and elastic properties of BeX at high pressure― Indian Journal of Physics, 2016, 90, 1243-1244. | 1.8 | 3 |
| 10 | Temperature dependence of the inhomogeneous parameters of the Mo/4H–SiC Schottky barrier diodes. Semiconductor Science and Technology, 2016, 31, 085008. | 2.0 | 12 |
| 11 | Comment on "Debye temperature and melting point of Ilâ€VI and Illâ€V semiconductors―[Cryst. Res. Technol. 45, No. 9, 920–924 (2010)]. Crystal Research and Technology, 2016, 51, 115-116. | 1.3 | 3 |
| 12 | New study of the abnormal behavior of the low temperature dependence of the current in inhomogeneous Schottky diode. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2015, 28, 231-238. | 1.9 | 2 |
| 13 | Reverse bias-dependence of schottky barrier height on silicon carbide: influence of the temperature and donor concentration. International Journal of Physical Research, 2014, 2, . | 0.5 | 7 |
| 14 | Modified Airy function method modelling of tunnelling current for Schottky barrier diodes on silicon carbide. Semiconductor Science and Technology, 2013, 28, 105003. | 2.0 | 15 |
| 15 | Electrical characteristics of Mo/4H-SiC Schottky diodes having ion-implanted guard rings: temperature and implant-dose dependence. Semiconductor Science and Technology, 2011, 26, 085003. | 2.0 | 20 |